

alloy layer is provided having the melting point higher than that of a solder having Pb as a main composition metal, wherein said alloy layer contains no Pb and no Pd as a main composing metal; and

a resin molding said connected first portion,

wherein said alloy layer is provided at a second portion of said connected member outside of said resin. (see ...)

3. (Amended) A semiconductor integrated circuit device comprising:

a conductive connecting member;

a connected member in which a metal layer including a palladium layer is provided at a first portion to which said connecting member is connected, and a metal layer is provided having the melting point higher than that of an Sn-Pb eutectic solder, wherein said metal layer contains no Pb and no Pd as a main composing metal; and

a resin molding said connected first portion,

wherein said metal layer is provided at a second portion of said connected member outside of said resin.

4. (Amended) A semiconductor integrated circuit device comprising:

a conductive connecting member;

a connected member in which a metal layer including a palladium layer is provided at a first portion to which said connecting member is connected, and a Pb-layer, having the melting point higher than Sn-Pb eutectic solder, wherein said Pb-free metal layer contains no Pd as a main composing metal; and

a resin molding said connected first portion,

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cont.

wherein said Pb-free metal layer is provided at a second portion of said connected member outside of said resin.

5. (Amended) A semiconductor integrated circuit device comprising:

a semiconductor chip;

a conductive connecting member connected to said semiconductor chip;

a connected member in which a metal layer including a palladium layer is provided at a first portion to which said connecting member is connected, and a Pb-free metal layer having the melting point higher than that of an Sn-Pb eutectic solder, wherein said Pb-free metal layer contains no Pd as a main composing metal, wherein said Pb-free metal layer is provided in a second portion of the connected member other than said first portion; and

a resin molding said semiconductor chip connected to said connecting portion, said connecting member and said first portion of said connected portion to which said connecting member is connected.

6. (Amended) A semiconductor integrated circuit device comprising:

a semiconductor chip;

a wire bonded to said semiconductor chip;

a lead including an inner lead portion and an outer lead portion, wherein a metal layer including a palladium layer is plated on said inner lead portion and is bonded to said wire, and wherein a Pb-free alternate solder, having the melting point higher than that of an Sn-Pb eutectic solder, and which Pb-free alternate solder contains no Pd as a main composing metal, is plated on a mounted portion of said

outer lead portion; and

a resin molding a bonding portion of said semiconductor chip to which said wire is bonded, said wire and the inner lead portion of said lead to which said wire is bonded.

7. (Amended) A semiconductor integrated circuit device comprising:

a semiconductor chip;

a wire;

a resin molding said semiconductor chip and

said wire; and

a lead in which a metal layer including a palladium layer is provided in a front end portion of said lead molded by said resin, and a Pb-free metal layer, having the melting point higher than an Sn-Pb eutectic solder, which Pb-free metal layer contains no Pd as a main composing metal, is provided at an outer portion of said lead which is not molded by said resin.

9. (Amended) A mounting substrate structure comprising:

a semiconductor integrated circuit device, said semiconductor integrated circuit device being provided with a conductive connecting member, a connected member in which a metal layer including a palladium layer is provided at a first portion to which said connecting member is connected, and an alloy containing no Pb and no Pd as a main composing metal is provided in a second portion of said connected member, and a resin molding said first portion of said connected member to be connected; and

a printed circuit board,

wherein said semiconductor integrated circuit device is connected to said printed circuit board by a solder having the melting point higher than that of a solder having Pb as a main composing metal and

wherein said second portion of said connected member is outside of said resin.

10. (Amended) A mounting substrate structure comprising:

β^2 a semiconductor integrated circuit device, said semiconductor integrated circuit device being provided with a conductive connecting member, a connected member in which a metal layer including a palladium layer is provided at a first portion to which said connecting member is connected, and a metal containing no Pb and no Pd as a main composing metal at a second portion, and a resin molding said first portion of said connected member to be connected to said connecting member; and

a printed circuit board to which said semiconductor integrated circuit device is connected by a metal having the melting point higher than that of a solder having Pb as a main composing metal,

wherein said second portion of said connected member is outside of said resin.

Please add claims 18-25 as follows:

β^3 -- 18. A semiconductor integrated circuit device according to claim 2, wherein said palladium layer is not provided at said second portion of the connected member outside of the resin.

19. A semiconductor integrated circuit device according to claim 3, wherein said palladium layer is not provided at said second portion of the connected member outside of the resin.

20. A semiconductor integrated circuit device according to claim 4, wherein said palladium layer is not provided at said second portion of the connected member outside of the resin.

21. A semiconductor integrated circuit device according to claim 5, wherein said palladium layer is not provided at said second portion of the connected member.

B³ 22. A semiconductor integrated circuit device according to claim 6, wherein said palladium layer is not provided at said outer lead portion of said lead.

23. A semiconductor integrated circuit device according to claim 7, wherein said palladium layer is not provided at said second portion of the connected member.

24. A mounting substrate structure according to claim 9, wherein said palladium layer is not provided at said second portion of the connected member outside of the resin.

25. A mounting substrate structure according to claim 10, wherein said palladium layer is not provided at said second portion of the connected member outside of the resin. --
